Amplifier Transistors NPN Silicon

COLLECTOR 3 BASE 1 EMITTER

MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector-Emitter Voltage	VCEO	140	160	Vdc
Collector-Base Voltage	V _{CBO}	160	180	Vdc
Emitter-Base Voltage	VEBO	6.0 V		
Collector Current — Continuous	IC	600		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	600 625 5.0		mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R_{θ} JC	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteris	stic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•			
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 1.0 mAdc, I _B = 0)	2N5550 2N5551	V(BR)CEO	140 160	_	Vdc
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	2N5550 2N5551	V _(BR) CBO	160 180		Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)		V(BR)EBO	6.0	_	Vdc
Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0) (V _{CB} = 120 Vdc, I _E = 0) (V _{CB} = 100 Vdc, I _E = 0, T _A = 100°C) (V _{CB} = 120 Vdc, I _E = 0, T _A = 100°C)	2N5550 2N5551 2N5550 2N5551	^I CBO	_ _ _ _	100 50 100 50	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)		I _{EBO}	_	50	nAdc

^{1.} Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle = 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

2N5550 2N5551*

*Motorola Preferred Device





2N5550 2N5551

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	2N5550 2N5551	hFE	60 80	_	_
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5550 2N5551		60 80	250 250	
$(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5550 2N5551		20 30	_ _	
Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc)	Both Types	V _{CE(sat)}	_	0.15	Vdc
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	2N5550 2N5551		_	0.25 0.20	
Base-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc)	Both Types	VBE(sat)	_	1.0	Vdc
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	2N5550 2N5551		_	1.2 1.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (IC = 10 mAdc, VCE = 10 Vdc, f = 100 MHz)		fΤ	100	300	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	6.0	pF
Input Capacitance (VEB = 0.5 Vdc, I _C = 0 , f = 1.0 MHz)	2N5550 2N5551	C _{ibo}		30 20	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	50	200	_
Noise Figure (I _C = 250 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	2N5550 2N5551	NF		10 8.0	dB

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

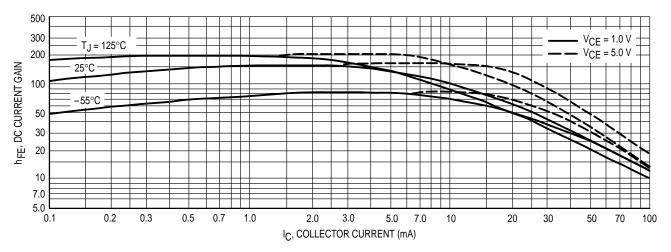


Figure 1. DC Current Gain

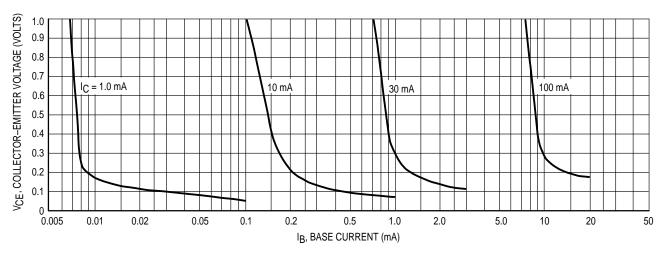


Figure 2. Collector Saturation Region

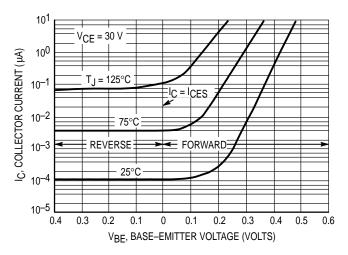


Figure 3. Collector Cut-Off Region

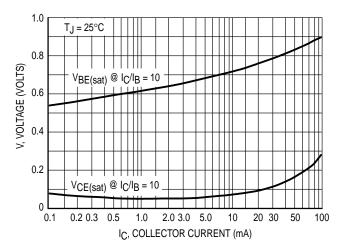


Figure 4. "On" Voltages

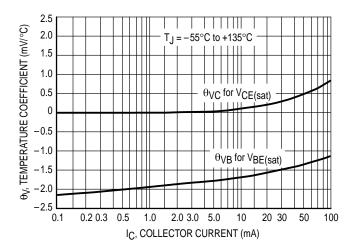


Figure 5. Temperature Coefficients

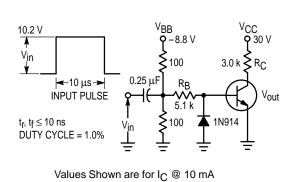


Figure 6. Switching Time Test Circuit

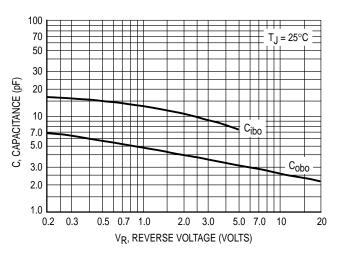


Figure 7. Capacitances

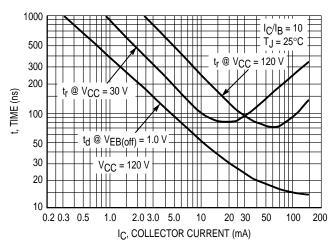


Figure 8. Turn-On Time

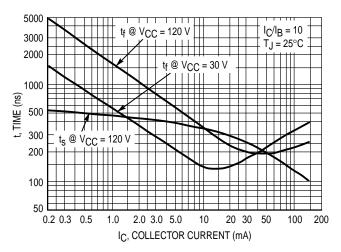
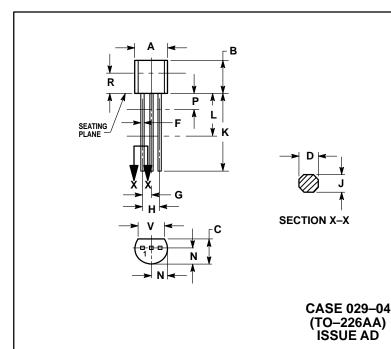


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	INCHES MIL		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1: PIN 1. EMITTER

2. BASE 3. COLLECTOR

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and (A) are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



